MOSFET - Single, N-Channel, Gate ESD Protection, Small Signal, SC-75

20 V, 238 mA

Features

- Low Gate Charge for Fast Switching
- Small 1.6 x 1.6 mm Footprint
- ESD Protected Gate
- AEC-Q101 Qualified and PPAP Capable NVA4001N
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Power Management Load Switch
- Level Shift
- Portable Applications such as Cell Phones, Media Players,
 Digital Cameras, PDA's, Video Games, Hand Held Computers, etc.

MAXIMUM RATINGS ($T_J = 25$ °C unless otherwise stated)

Paramo	Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	20	V
Gate-to-Source Voltage		V _{GS}	±10	V
Continuous Drain Current (Note 1)	I _D	238	mA	
Power Dissipation (Note 1) Steady State = 25°C		P _D	300	mW
Pulsed Drain Current	I _{DM}	714	mA	
Operating Junction and St	T _J , T _{STG}	–55 to 150	°C	
Continuous Source Curre	I _{SD}	238	mA	
Lead Temperature for Solo (1/8" from case for 10 s)	TL	260	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	416	°C/W

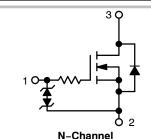
Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).



ON Semiconductor®

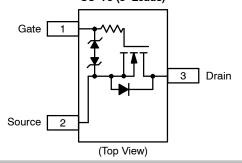
http://onsemi.com

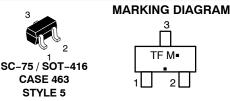
V _{(BR)DSS}	R _{DS(on)} Typ @ V _{GS}	I _D MAX (Note 1)
20 V	1.5 Ω @ 4.5 V	238 mA
	2.2 Ω @ 2.5 V	200



PIN CONNECTIONS

SC-75 (3-Leads)





TF = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 100 \mu\text{A}$	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 20 V			1.0	μΑ
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±10 V			±100	μΑ
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(TH)}	$V_{DS} = 3 \text{ V}, I_{D} = 100 \mu\text{A}$	0.5	1.0	1.5	V
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 10 mA		1.5	3.0	
		V _{GS} = 2.5 V, I _D = 10 mA		2.2	3.5	Ω
Forward Transconductance	9FS	$V_{DS} = 3 \text{ V}, I_{D} = 10 \text{ mA}$		80		mS
CAPACITANCES						
Input Capacitance	C _{ISS}			11.5	20	
Output Capacitance	Coss	$V_{DS} = 5 \text{ V, f} = 1 \text{ MHz,} $ $V_{GS} = 0 \text{ V}$		10	15	pF
Reverse Transfer Capacitance	C _{RSS}	143 01		3.5	6.0	
SWITCHING CHARACTERISTICS (Note 3)						
Turn-On Delay Time	t _{d(ON)}			13		ns
Rise Time	t _r	V _{GS} = 4.5 V, V _{DS} = 5 V,		15		
Turn-Off Delay Time	t _{d(OFF)}	$I_D = 10 \text{ mA}, R_G = 10 \Omega$		98		ns
Fall Time	t _f			60		1
DRAIN-SOURCE DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	$V_{GS} = 0 \text{ V}, I_{S} = 10 \text{ mA}$		0.66	8.0	V

Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

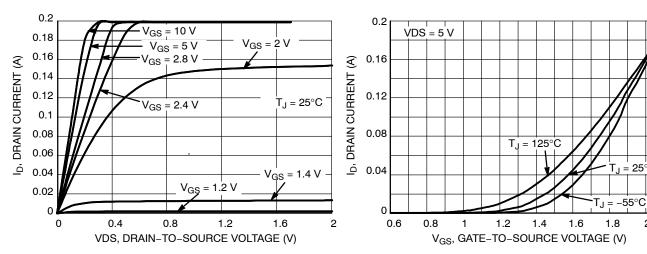


Figure 1. On-region Characteristics

Figure 2. Transfer Characteristics

T_J = 25 o C

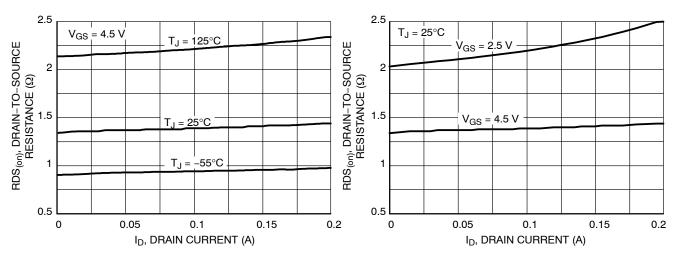


Figure 3. On-resistance versus Drain Current and Temperature

Figure 4. On-resistance versus Drain Current and Gate Voltage

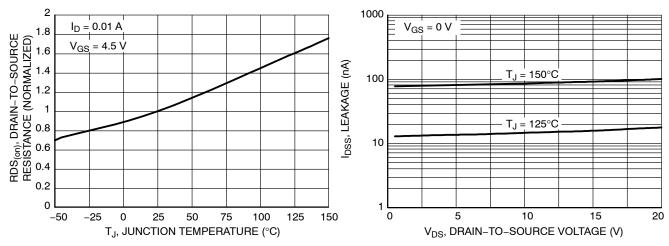
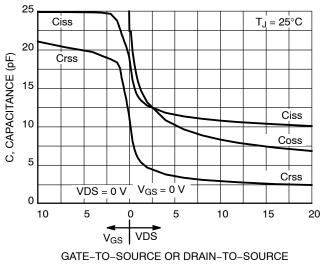


Figure 5. On-resistance Variation with **Temperature**

Figure 6. Drain-to-Source Leakage Current versus Voltage

TYPICAL PERFORMANCE CURVES



 $\begin{array}{c} 1000 \\ \hline V_{DD} = 5 \, V \\ \hline I_D = 10 \, \text{mA} \\ \hline V_{GS} = 4.5 \, V \\ \hline \end{array}$

GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (V)

Figure 8. Resistive Switching Time Variation versus Gate Resistance



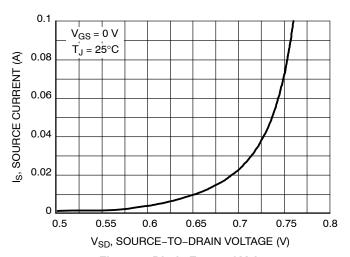


Figure 9. Diode Forward Voltage versus Current

ORDERING INFORMATION

Order Number	Package	Shipping [†]
NTA4001NT1G	SC-75 (Pb-Free)	3000 / Tape & Reel
NVA4001NT1G	SC-75 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

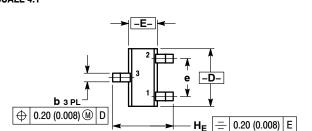
MECHANICAL CASE OUTLINE

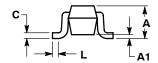




SC-75/SOT-416 CASE 463-01 ISSUE G

DATE 07 AUG 2015





STYLE 1: PIN 1. BASE 2. EMITTER

STYLE 4:

3. COLLECTOR

PIN 1. CATHODE 2. CATHODE 3. ANODE

STYLE 5: PIN 1. GATE 2. SOURCE

3. DRAIN

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE

STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

		MILLIMETERS			INCHES		
DII	И	MIN	NOM	MAX	MIN	NOM	MAX
Α		0.70	0.80	0.90	0.027	0.031	0.035
A	1	0.00	0.05	0.10	0.000	0.002	0.004
b		0.15	0.20	0.30	0.006	0.008	0.012
С		0.10	0.15	0.25	0.004	0.006	0.010
D		1.55	1.60	1.65	0.061	0.063	0.065
E		0.70	0.80	0.90	0.027	0.031	0.035
е		1.00 BSC			0.04 BSC		
L		0.10	0.15	0.20	0.004	0.006	0.008
HE	:	1.50	1.60	1.70	0.060	0.063	0.067

GENERIC MARKING DIAGRAM*

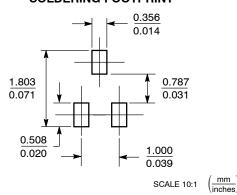


XX= Specific Device Code

Μ = Date Code

= Pb-Free Package

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SC-75/SOT-416		PAGE 1 OF 1	

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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Phone: 00421 33 790 2910

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